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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	1232
Number of Logic Elements/Cells	-
Total RAM Bits	-
Number of I/O	140
Number of Gates	8000
Voltage - Supply	4.5V ~ 5.5V
Mounting Type	Through Hole
Operating Temperature	-55°C ~ 125°C (TJ)
Package / Case	176-BCPGA
Supplier Device Package	176-CPGA (39.88x39.88)
Purchase URL	https://www.e-xfl.com/product-detail/microsemi/5962-9215601mxa

2 – Detailed Specifications

Operating Conditions

Table 2-1 • **Absolute Maximum Ratings[1]**

Symbol	Parameter	Limits	Units
VCC	DC supply voltage	–0.5 to +7.0	V
VI	Input voltage	–0.5 to VCC + 0.5	V
VO	Output voltage	–0.5 to VCC + 0.5	V
IIO	I/O source sink current[2]	±20	mA
T_{STG}	Storage temperature	–65 to +150	°C

Notes:

1. *Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. Exposure to absolute maximum rated conditions for extended periods may affect device reliability. Device should not be operated outside the recommended operating conditions.*
2. *Device inputs are normally high impedance and draw extremely low current. However, when input voltage is greater than VCC + 0.5 V for less than GND –0.5 V, the internal protection diodes will be forward biased and can draw excessive current.*

Table 2-2 • **Recommended Operating Conditions**

Parameter	Commercial	Industrial	Military	Units
Temperature range*	0 to +70	–40 to +85	–55 to +125	°C
Power supply tolerance	±5	±10	±10	%VCC

*Note: *Ambient temperature (T_A) is used for commercial and industrial; case temperature (T_C) is used for military.*

Table 2-3 • **Electrical Specifications**

Symbol	Parameter	Commercial		Industrial		Military		Units
		Min.	Max.	Min.	Max.	Min.	Max.	
VOH[1]	(IOH = –10 mA)[2]	2.4	–	–	–	–	–	V
	(IOH = –6 mA)	3.84	–	–	–	–	–	V
	(IOH = –4 mA)	–	–	3.7	–	3.7	–	V
VOL[1]	(IOL = 10 mA)[2]	–	0.5	–	–	–	–	V
	(IOL = 6 mA)	–	0.33	–	0.40	–	0.40	V
VIL		–0.3	0.8	–0.3	0.8	–0.3	0.8	V
VIH		2.0	VCC + 0.3	2.0	VCC + 0.3	2.0	VCC + 0.3	V
Input Transition Time t_R, t_F[2]		–	500	–	500	–	500	ns
C_{IO} I/O capacitance[2,3]		–	10	–	10	–	10	pF
Standby Current, ICC[4] (typical = 1 mA)		–	2	–	10	–	20	mA
Leakage Current[5]		–10	+10	–10	+10	–10	+10	µA
ICC(D)	Dynamic VCC supply current. See the Power Dissipation section.							

Notes:

1. *Only one output tested at a time. VCC = minimum.*
2. *Not tested, for information only.*
3. *Includes worst-case PG176 package capacitance. VOUT = 0 V, f = 1 MHz*
4. *All outputs unloaded. All inputs = VCC or GND, typical ICC = 1 mA. ICC limit includes IPP and ISV during normal operations.*
5. *VOUT, VIN = VCC or GND.*

Package Thermal Characteristics

The device junction to case thermal characteristic is θjc, and the junction to ambient air characteristic is θja. The thermal characteristics for θja are shown with two different air flow rates.

Maximum junction temperature is 150°C.

A sample calculation of the absolute maximum power dissipation allowed for a PQ160 package at commercial temperature and still air is as follows:

$$\frac{\text{Max. junction temp. (°C)} - \text{Max. ambient temp. (°C)}}{\theta_{ja}\text{°C/W}} = \frac{150\text{°C} - 70\text{°C}}{33\text{°C/W}} = 2.4\ \text{W}$$

EQ 1

Table 2-4 • **Package Thermal Characteristics**

Package Type*	**Pin Count**	θ_{jc}	θ_{ja} **Still Air**	θ_{ja} **300 ft./min.**	**Units**
Ceramic Pin Grid Array	100	5	35	17	°C/W
	132	5	30	15	°C/W
	176	8	23	12	°C/W
Ceramic Quad Flatpack	172	8	25	15	°C/W
Plastic Quad Flatpack[1]	100	13	48	40	°C/W
	144	15	40	32	°C/W
	160	15	38	30	°C/W
Plastic Leaded Chip Carrier	84	12	37	28	°C/W
Very Thin Quad Flatpack	100	12	43	35	°C/W
Thin Quad Flatpack	176	15	32	25	°C/W

Notes: (Maximum Power in Still Air)

1. *Maximum power dissipation values for PQFP packages are 1.9 W (PQ100), 2.3 W (PQ144), and 2.4 W (PQ160).*
2. *Maximum power dissipation for PLCC packages is 2.7 W.*
3. *Maximum power dissipation for VQFP packages is 2.3 W.*
4. *Maximum power dissipation for TQFP packages is 3.1 W.*

Power Dissipation

$$P = [I_{CC\ standby} + I_{CCactive}] * V_{CC} + I_{OL} * V_{OL} * N + I_{OH} * (V_{CC} - V_{OH}) * M$$

EQ 2

where:

$I_{CC\ standby}$ is the current flowing when no inputs or outputs are changing

$I_{CCactive}$ is the current flowing due to CMOS switching.

I_{OL} and I_{OH} are TTL sink/source currents.

V_{OL} and V_{OH} are TTL level output voltages.

N is the number of outputs driving TTL loads to V_{OL}.

M is the number of outputs driving TTL loads to V_{OH}.

An accurate determination of N and M is problematical because their values depend on the family type, design details, and on the system I/O. The power can be divided into two components: static and active.

Static Power Component

Microsemi FPGAs have small static power components that result in lower power dissipation than PALs or PLDs. By integrating multiple PALs/PLDs into one FPGA, an even greater reduction in board-level power dissipation can be achieved.

The power due to standby current is typically a small component of the overall power. Standby power is calculated in Table 2-5 for commercial, worst case conditions.

Table 2-5 • **Standby Power Calculation**

ICC	VCC	Power
2 mA	5.25 V	10.5 mW

The static power dissipated by TTL loads depends on the number of outputs driving high or low and the DC load current. Again, this value is typically small. For instance, a 32-bit bus sinking 4 mA at 0.33 V will generate 42 mW with all outputs driving low, and 140 mW with all outputs driving high. The actual dissipation will average somewhere between as I/Os switch states with time.

Active Power Component

Power dissipation in CMOS devices is usually dominated by the active (dynamic) power dissipation. This component is frequency dependent, a function of the logic and the external I/O. Active power dissipation results from charging internal chip capacitances of the interconnect, unprogrammed antifuses, module inputs, and module outputs, plus external capacitance due to PC board traces and load device inputs.

An additional component of the active power dissipation is the totem-pole current in CMOS transistor pairs. The net effect can be associated with an equivalent capacitance that can be combined with frequency and voltage to represent active power dissipation.

Equivalent Capacitance

The power dissipated by a CMOS circuit can be expressed by EQ 3.

$$\text{Power } (\mu W) = C_{EQ} * VCC^2 * F \qquad \textit{EQ 3}$$

Where:

C_{EQ} is the equivalent capacitance expressed in pF.

VCC is the power supply in volts.

F is the switching frequency in MHz.

Equivalent capacitance is calculated by measuring ICC active at a specified frequency and voltage for each circuit component of interest. Measurements have been made over a range of frequencies at a fixed value of VCC. Equivalent capacitance is frequency independent so that the results may be used over a wide range of operating conditions. Equivalent capacitance values are shown in Table 2-6.

Table 2-6 • **CEQ Values for Microsemi FPGAs**

Item	CEQ Value
Modules (C_{EQM})	5.8
Input Buffers (C_{EQI})	12.9
Output Buffers (C_{EQO})	23.8
Routed Array Clock Buffer Loads (C_{EQCR})	3.9

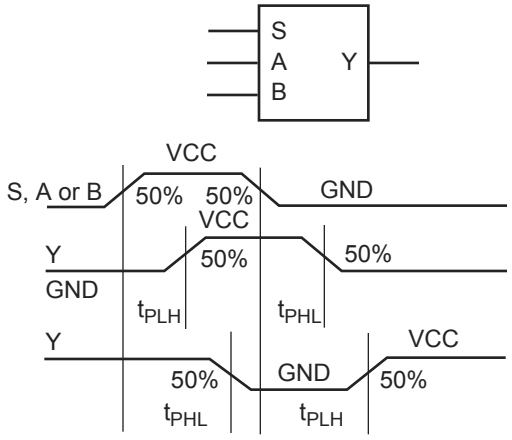
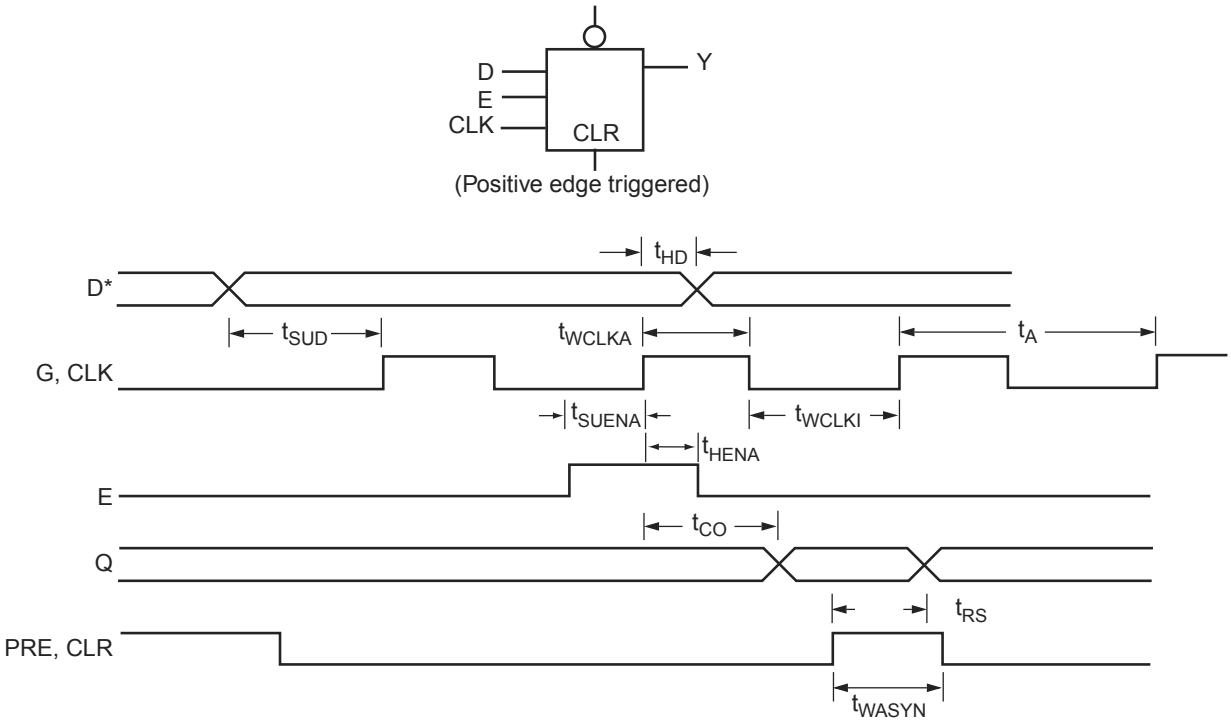


Figure 2-5 • **Module Delays**

Sequential Module Timing Characteristics



Note: D represents all data functions involving A, B, and S for multiplexed flip-flops.

Figure 2-6 • **Flip-Flops and Latches**

Timing Derating Factor (Temperature and Voltage)

Table 2-9 • **Timing Derating Factor (Temperature and Voltage)**

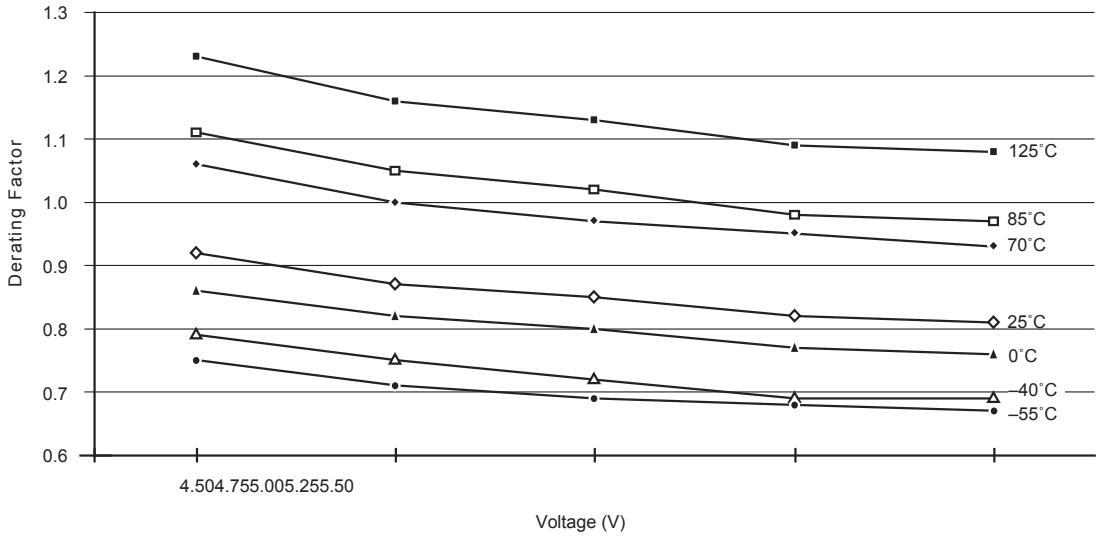
(Commercial Minimum/Maximum Specification) x	Industrial		Military	
	Min.	**Max.**	**Min.**	Max.
	0.69	1.11	0.67	1.23

Table 2-10 • **Timing Derating Factor for Designs at Typical Temperature (T_J = 25°C) and Voltage (5.0 V)**

(Commercial Maximum Specification) x	0.85

Table 2-11 • **Temperature and Voltage Derating Factors (normalized to Worst-Case Commercial, TJ = 4.75 V, 70°C)**

	–55	**–40**	**0**	**25**	**70**	**85**	**125**
4.50	0.75	0.79	0.86	0.92	1.06	1.11	1.23
4.75	0.71	0.75	0.82	0.87	1.00	1.05	1.13
5.00	0.69	0.72	0.80	0.85	0.97	1.02	1.13
5.25	0.68	0.69	0.77	0.82	0.95	0.98	1.09
5.50	0.67	0.69	0.76	0.81	0.93	0.97	1.08



Note: This derating factor applies to all routing and propagation delays.

Figure 2-9 • **Junction Temperature and Voltage Derating Curves (normalized to Worst-Case Commercial, T_J = 4.75 V, 70°C)**

A1225A Timing Characteristics (continued)

***Table 2-13* • A1225A Worst-Case Commercial Conditions, VCC = 4.75 V, T_J = 70°C**

I/O Module Input Propagation Delays			–2 Speed		–1 Speed		Std. Speed		Units
Parameter/Description			**Min.**	**Max.**	**Min.**	**Max.**	**Min.**	**Max.**	
t_{INYH}	Pad to Y High			2.9		3.3		3.8	ns
t_{INYL}	Pad to Y Low			2.6		3.0		3.5	ns
t_{INGH}	G to Y High			5.0		5.7		6.6	ns
t_{INGL}	G to Y Low			4.7		5.4		6.3	ns
Input Module Predicted Input Routing Delays*									
t_{IRD1}	FO = 1 Routing Delay			4.1		4.6		5.4	ns
t_{IRD2}	FO = 2 Routing Delay			4.6		5.2		6.1	ns
t_{IRD3}	FO = 3 Routing Delay			5.3		6.0		7.1	ns
t_{IRD4}	FO = 4 Routing Delay			5.7		6.4		7.6	ns
t_{IRD8}	FO = 8 Routing Delay			7.4		8.3		9.8	ns
Global Clock Network									
t_{CKH}	Input Low to High	FO = 32		10.2		11.0		12.8	ns
		FO = 256		11.8		13.0		15.7	
t_{CKL}	Input High to Low	FO = 32		10.2		11.0		12.8	ns
		FO = 256		12.0		13.2		15.9	
t_{PWH}	Minimum Pulse Width High	FO = 32	3.4		4.1		4.5		ns
		FO = 256	3.8		4.5		5.0		
t_{PWL}	Minimum Pulse Width Low	FO = 32	3.4		4.1		4.5		ns
		FO = 256	3.8		4.5		5.0		
t_{CKSW}	Maximum Skew	FO = 32		0.7		0.7		0.7	ns
		FO = 256		3.5		3.5		3.5	
t_{SUEXT}	Input Latch External Setup	FO = 32	0.0		0.0		0.0		ns
		FO = 256	0.0		0.0		0.0		
t_{HEXT}	Input Latch External Hold	FO = 32	7.0		7.0		7.0		ns
		FO = 256	11.2		11.2		11.2		
t_P	Minimum Period	FO = 32	7.7		8.3		9.1		ns
		FO = 256	8.1		8.8		10.0		
f_{MAX}	Maximum Frequency	FO = 32		130.0		120.0		110.0	ns
		FO = 256		125.0		115.0		100.0	

*Note: *These parameters should be used for estimating device performance. Optimization techniques may further reduce delays by 0 to 4 ns. Routing delays are for typical designs across worst-case operating conditions. Post-route timing analysis or simulation is required to determine actual worst-case performance. Post-route timing is based on actual routing delay measurements performed on the device prior to shipment.*

A1225A Timing Characteristics (continued)

***Table 2-14* • A1225A Worst-Case Commercial Conditions, VCC = 4.75 V, T_J = 70°C**

TTL Output Module Timing[1]		–2 Speed		–1 Speed		Std. Speed		Units
Parameter/Description		**Min.**	**Max.**	**Min.**	**Max.**	**Min.**	**Max.**	
t_{DLH}	Data to Pad High		8.0		9.0		10.6	ns
t_{DHL}	Data to Pad Low		10.1		11.4		13.4	ns
t_{ENZH}	Enable Pad Z to High		8.9		10.0		11.8	ns
t_{ENZL}	Enable Pad Z to Low		11.6		13.2		15.5	ns
t_{ENHZ}	Enable Pad High to Z		7.1		8.0		9.4	ns
t_{ENLZ}	Enable Pad Low to Z		8.3		9.5		11.1	ns
t_{GLH}	G to Pad High		8.9		10.2		11.9	ns
t_{GHL}	G to Pad Low		11.2		12.7		14.9	ns
d_{TLH}	Delta Low to High		0.07		0.08		0.09	ns/pF
d_{THL}	Delta High to Low		0.12		0.13		0.16	ns/pF
CMOS Output Module Timing[1]								
t_{DLH}	Data to Pad High		10.1		11.5		13.5	ns
t_{DHL}	Data to Pad Low		8.4		9.6		11.2	ns
t_{ENZH}	Enable Pad Z to High		8.9		10.0		11.8	ns
t_{ENZL}	Enable Pad Z to Low		11.6		13.2		15.5	ns
t_{ENHZ}	Enable Pad High to Z		7.1		8.0		9.4	ns
t_{ENLZ}	Enable Pad Low to Z		8.3		9.5		11.1	ns
t_{GLH}	G to Pad High		8.9		10.2		11.9	ns
t_{GHL}	G to Pad Low		11.2		12.7		14.9	ns
d_{TLH}	Delta Low to High		0.12		0.13		0.16	ns/pF
d_{THL}	Delta High to Low		0.09		0.10		0.12	ns/pF

Notes:

1. *Delays based on 50 pF loading.*
2. *SSO information can be found at www.microsemi.com/soc/techdocs/appnotes/board_consideration.aspx.*

A1240A Timing Characteristics (continued)

***Table 2-16* • A1240A Worst-Case Commercial Conditions, VCC = 4.75 V, T_J = 70°C**

I/O Module Input Propagation Delays			–2 Speed		–1 Speed		Std. Speed		Units
Parameter/Description			**Min.**	**Max.**	**Min.**	**Max.**	**Min.**	**Max.**	
t_{INYH}	Pad to Y High			2.9		3.3		3.8	ns
t_{INYL}	Pad to Y Low			2.6		3.0		3.5	ns
t_{INGH}	G to Y High			5.0		5.7		6.6	ns
t_{INGL}	G to Y Low			4.7		5.4		6.3	ns
Input Module Predicted Input Routing Delays*									
t_{IRD1}	FO = 1 Routing Delay			4.2		4.8		5.6	ns
t_{IRD2}	FO = 2 Routing Delay			4.8		5.4		6.4	ns
t_{IRD3}	FO = 3 Routing Delay			5.4		6.1		7.2	ns
t_{IRD4}	FO = 4 Routing Delay			5.9		6.7		7.9	ns
t_{IRD8}	FO = 8 Routing Delay			7.9		8.9		10.5	ns
Global Clock Network									
t_{CKH}	Input Low to High	FO = 32		10.2		11.0		12.8	ns
		FO = 256		11.8		13.0		15.7	
t_{CKL}	Input High to Low	FO = 32		10.2		11.0		12.8	ns
		FO = 256		12.0		13.2		15.9	
t_{PWH}	Minimum Pulse Width High	FO = 32	3.8		4.5		5.5		ns
		FO = 256	4.1		5.0		5.8		
t_{PWL}	Minimum Pulse Width Low	FO = 32	3.8		4.5		5.5		ns
		FO = 256	4.1		5.0		5.8		
t_{CKSW}	Maximum Skew	FO = 32		0.5		0.5		0.5	ns
		FO = 256		2.5		2.5		2.5	
t_{SUEXT}	Input Latch External Setup	FO = 32	0.0		0.0		0.0		ns
		FO = 256	0.0		0.0		0.0		
t_{HEXT}	Input Latch External Hold	FO = 32	7.0		7.0		7.0		ns
		FO = 256	11.2		11.2		11.2		
t_P	Minimum Period	FO = 32	8.1		9.1		11.1		ns
		FO = 256	8.8		10.0		11.7		
f_{MAX}	Maximum Frequency	FO = 32		125.0		110.0		90.0	ns
		FO = 256		115.0		100.0		85.0	

*Note: *These parameters should be used for estimating device performance. Optimization techniques may further reduce delays by 0 to 4 ns. Routing delays are for typical designs across worst-case operating conditions. Post-route timing analysis or simulation is required to determine actual worst-case performance. Post-route timing is based on actual routing delay measurements performed on the device prior to shipment.*

A1280A Timing Characteristics

***Table 2-18* • A1280A Worst-Case Commercial Conditions, VCC = 4.75 V, T_J = 70°C**

Logic Module Propagation Delays[1]		**–2 Speed[3]**		**–1 Speed**		**Std. Speed**		**Units**
Parameter/Description		**Min.**	**Max.**	**Min.**	**Max.**	**Min.**	**Max.**	
t_{PD1}	Single Module		3.8		4.3		5.0	ns
t_{CO}	Sequential Clock to Q		3.8		4.3		5.0	ns
t_{GO}	Latch G to Q		3.8		4.3		5.0	ns
t_{RS}	Flip-Flop (Latch) Reset to Q		3.8		4.3		5.0	ns
Predicted Routing Delays[2]								
t_{RD1}	FO = 1 Routing Delay		1.7		2.0		2.3	ns
t_{RD2}	FO = 2 Routing Delay		2.5		2.8		3.3	ns
t_{RD3}	FO = 3 Routing Delay		3.0		3.4		4.0	ns
t_{RD4}	FO = 4 Routing Delay		3.7		4.2		4.9	ns
t_{RD8}	FO = 8 Routing Delay		6.7		7.5		8.8	ns
Sequential Timing Characteristics[3,4]								
t_{SUD}	Flip-Flop (Latch) Data Input Setup	0.4		0.4		0.5		ns
t_{HD}	Flip-Flop (Latch) Data Input Hold	0.0		0.0		0.0		ns
t_{SUENA}	Flip-Flop (Latch) Enable Setup	0.8		0.9		1.0		ns
t_{HENA}	Flip-Flop (Latch) Enable Hold	0.0		0.0		0.0		ns
t_{WCLKA}	Flip-Flop (Latch) Clock Active Pulse Width	5.5		6.0		7.0		ns
t_{WASYN}	Flip-Flop (Latch) Clock Asynchronous Pulse Width	5.5		6.0		7.0		ns
t_A	Flip-Flop Clock Input Period	11.7		13.3		18.0		ns
t_{INH}	Input Buffer Latch Hold	0.0		0.0		0.0		ns
t_{INSU}	Input Buffer Latch Setup	0.4		0.4		0.5		ns
t_{OUTH}	Output Buffer Latch Hold	0.0		0.0		0.0		ns
t_{OUTSU}	Output Buffer Latch Setup	0.4		0.4		0.5		ns
f_{MAX}	Flip-Flop (Latch) Clock Frequency		85.0		75.0		50.0	MHz

Notes:

1. *For dual-module macros, use $t_{PD1} + t_{RD1} + t_{PDn}$, $t_{CO} + t_{RD1} + t_{PDn}$, or $t_{PD1} + t_{RD1} + t_{SUD}$—whichever is appropriate.*
2. *Routing delays are for typical designs across worst-case operating conditions. These parameters should be used for estimating device performance. Post-route timing analysis or simulation is required to determine actual worst-case performance. Post-route timing is based on actual routing delay measurements performed on the device prior to shipment.*
3. *Data applies to macros based on the S-module. Timing parameters for sequential macros constructed from C-modules can be obtained from the DirectTime Analyzer utility.*
4. *Setup and hold timing parameters for the Input Buffer Latch are defined with respect to the PAD and the D input. External setup/hold timing parameters must account for delay from an external PAD signal to the G inputs. Delay from an external PAD signal to the G input subtracts (adds) to the internal setup (hold) time.*

A1280A Timing Characteristics (continued)

***Table 2-19* • A1280A Worst-Case Commercial Conditions, VCC = 4.75 V, T_J = 70°C**

I/O Module Input Propagation Delays			–2 Speed		–1 Speed		Std. Speed		Units
Parameter/Description			**Min.**	**Max.**	**Min.**	**Max.**	**Min.**	**Max.**	
t_{INYH}	Pad to Y High			2.9		3.3		3.8	ns
t_{INYL}	Pad to Y Low			2.7		3.0		3.5	ns
t_{INGH}	G to Y High			5.0		5.7		6.6	ns
t_{INGL}	G to Y Low			4.8		5.4		6.3	ns
Input Module Predicted Input Routing Delays*									
t_{IRD1}	FO = 1 Routing Delay			4.6		5.1		6.0	ns
t_{IRD2}	FO = 2 Routing Delay			5.2		5.9		6.9	ns
t_{IRD3}	FO = 3 Routing Delay			5.6		6.3		7.4	ns
t_{IRD4}	FO = 4 Routing Delay			6.5		7.3		8.6	ns
t_{IRD8}	FO = 8 Routing Delay			9.4		10.5		12.4	ns
Global Clock Network									
t_{CKH}	Input Low to High	FO = 32		10.2		11.0		12.8	ns
		FO = 256		13.1		14.6		17.2	
t_{CKL}	Input High to Low	FO = 32		10.2		11.0		12.8	ns
		FO = 256		13.3		14.9		17.5	
t_{PWH}	Minimum Pulse Width High	FO = 32	5.0		5.5		6.6		ns
		FO = 256	5.8		6.4		7.6		
t_{PWL}	Minimum Pulse Width Low	FO = 32	5.0		5.5		6.6		ns
		FO = 256	5.8		6.4		7.6		
t_{CKSW}	Maximum Skew	FO = 32		0.5		0.5		0.5	ns
		FO = 256		2.5		2.5		2.5	
t_{SUEXT}	Input Latch External Setup	FO = 32	0.0		0.0		0.0		ns
		FO = 256	0.0		0.0		0.0		
t_{HEXT}	Input Latch External Hold	FO = 32	7.0		7.0		7.0		ns
		FO = 256	11.2		11.2		11.2		
t_P	Minimum Period	FO = 32	9.6		11.2		13.3		ns
		FO = 256	10.6		12.6		15.3		
f_{MAX}	Maximum Frequency	FO = 32		105.0		90.0		75.0	ns
		FO = 256		95.0		80.0		65.0	

*Note: *These parameters should be used for estimating device performance. Optimization techniques may further reduce delays by 0 to 4 ns. Routing delays are for typical designs across worst-case operating conditions. Post-route timing analysis or simulation is required to determine actual worst-case performance. Post-route timing is based on actual routing delay measurements performed on the device prior to shipment.*

A1280A Timing Characteristics (continued)

Pin Descriptions

CLKA Clock A (Input)

TTL Clock input for clock distribution networks. The Clock input is buffered prior to clocking the logic modules. This pin can also be used as an I/O.

CLKB Clock B (Input)

TTL Clock input for clock distribution networks. The Clock input is buffered prior to clocking the logic modules. This pin can also be used as an I/O.

DCLK Diagnostic Clock (Input)

TTL Clock input for diagnostic probe and device programming. DCLK is active when the MODE pin is High. This pin functions as an I/O when the MODE pin is Low.

GND Ground

Low supply voltage.

I/O Input/Output (Input, Output)

The I/O pin functions as an input, output, three-state, or bidirectional buffer. Input and output levels are compatible with standard TTL and CMOS specifications. Unused I/O pins are automatically driven Low by the ALS software.

MODE Mode (Input)

The MODE pin controls the use of multifunction pins (DCLK, PRA, PRB, SDI). When the MODE pin is High, the special functions are active. When the MODE pin is Low, the pins function as I/Os. To provide Actionprobe capability, the MODE pin should be terminated to GND through a 10K resistor so that the MODE pin can be pulled High when required.

NC No Connection

This pin is not connected to circuitry within the device.

PRA Probe A (Output)

The Probe A pin is used to output data from any user-defined design node within the device. This independent diagnostic pin can be used in conjunction with the Probe B pin to allow real-time diagnostic output of any signal path within the device. The Probe A pin can be used as a user-defined I/O when debugging has been completed. The pin's probe capabilities can be permanently disabled to protect programmed design confidentiality. PRA is active when the MODE pin is High. This pin functions as an I/O when the MODE pin is Low.

PRB Probe B (Output)

The Probe B pin is used to output data from any user-defined design node within the device. This independent diagnostic pin can be used in conjunction with the Probe A pin to allow real-time diagnostic output of any signal path within the device. The Probe B pin can be used as a user-defined I/O when debugging has been completed. The pin's probe capabilities can be permanently disabled to protect programmed design confidentiality. PRB is active when the MODE pin is High. This pin functions as an I/O when the MODE pin is Low.

SDI Serial Data Input (Input)

Serial data input for diagnostic probe and device programming. SDI is active when the MODE pin is High. This pin functions as an I/O when the MODE pin is Low.

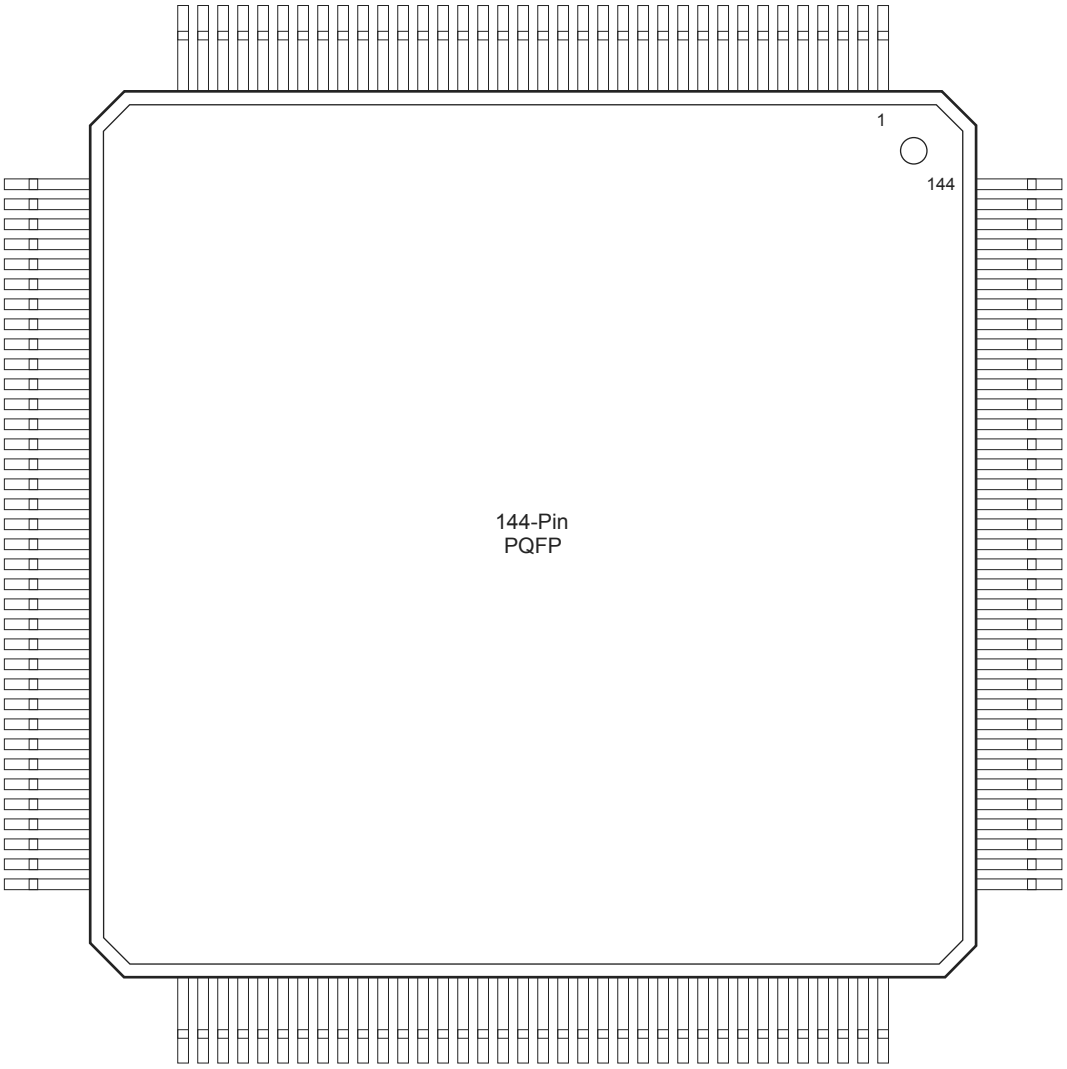
SDO Serial Data Output (Output)

Serial data output for diagnostic probe. SDO is active when the MODE pin is High. This pin functions as an I/O when the MODE pin is Low.

VCC 5.0 V Supply Voltage

High supply voltage.

PQ144



Note

For Package Manufacturing and Environmental information, visit the Resource Center at http://www.microsemi.com/soc/products/solutions/package/docs.aspx

PQ144	
Pin Number	**A1240A Function**
2	MODE
9	GND
10	GND
11	GND
18	VCC
19	VCC
20	VCC
21	VCC
28	GND
29	GND
30	GND
44	GND
45	GND
46	GND
54	VCC
55	VCC
56	VCC
64	GND
65	GND
71	SDO
79	GND
80	GND
81	GND
88	GND

PQ144	
Pin Number	**A1240A Function**
89	VCC
90	VCC
91	VCC
92	VCC
93	VCC
100	GND
101	GND
102	GND
110	SDI, I/O
116	GND
117	GND
118	GND
123	PRA, I/O
125	CLKA, I/O
126	VCC
127	VCC
128	VCC
130	CLKB, I/O
132	PRB, I/O
136	GND
137	GND
138	GND
144	DCLK, I/O

Notes:

1. All unlisted pin numbers are user I/Os.
2. MODE pin should be terminated to GND through a 10K resistor to enable Actionprobe usage; otherwise it can be terminated directly to GND.

PQ160	
Pin Number	**A1280A Function**
2	DCLK, I/O
6	VCC
11	GND
16	PRB, I/O
18	CLKB, I/O
20	VCC
21	CLKA, I/O
23	PRA, I/O
30	GND
35	VCC
38	SDI, I/O
40	GND
44	GND
49	GND
54	VCC
57	VCC
58	VCC
59	GND
60	VCC
61	GND
64	GND

PQ160	
Pin Number	**A1280A Function**
69	GND
80	GND
82	SDO
86	VCC
89	GN
98	GND
99	GND
109	GND
114	VCC
120	GND
125	GND
130	GND
135	VCC
138	VCC
139	VCC
140	GND
145	GND
150	VCC
155	GND
159	MODE
160	GND

Notes:

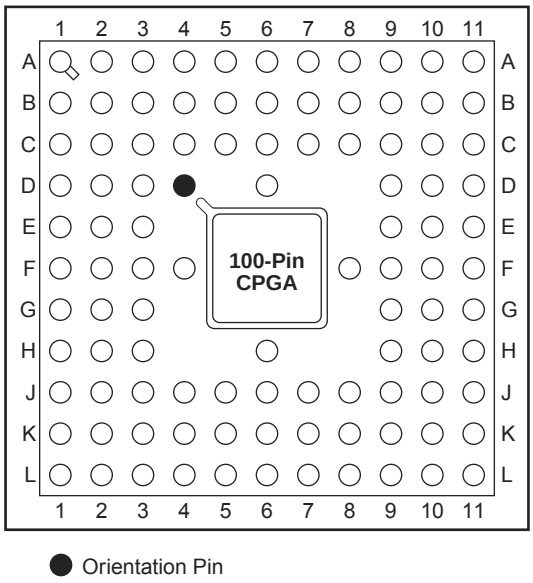
1. All unlisted pin numbers are user I/Os.
2. MODE pin should be terminated to GND through a 10K resistor to enable Actionprobe usage; otherwise it can be terminated directly to GND.

TQ176		
Pin Number	**A1240A Function**	**A1280A Function**
155	VCC	VCC
156	GND	GND
158	CLKB, I/O	CLKB, I/O
160	PRB, I/O	PRB, I/O
161	NC	I/O
165	NC	NC
166	NC	I/O
168	NC	I/O
170	NC	VCC
173	NC	I/O
175	DCLK, I/O	DCLK, I/O

Notes:

1. NC denotes no connection.
2. All unlisted pin numbers are user I/Os.
3. MODE pin should be terminated to GND through a 10K resistor to enable Actionprobe usage; otherwise it can be terminated directly to GND.

PG100



Note

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Datasheet Categories

Categories

In order to provide the latest information to designers, some datasheet parameters are published before data has been fully characterized from silicon devices. The data provided for a given device is designated as either "Product Brief," "Advance," "Preliminary," or "Production." The definitions of these categories are as follows:

Product Brief

The product brief is a summarized version of a datasheet (advance or production) and contains general product information. This document gives an overview of specific device and family information.

Advance

This version contains initial estimated information based on simulation, other products, devices, or speed grades. This information can be used as estimates, but not for production. This label only applies to the DC and Switching Characteristics chapter of the datasheet and will only be used when the data has not been fully characterized.

Preliminary

The datasheet contains information based on simulation and/or initial characterization. The information is believed to be correct, but changes are possible.

Production

This version contains information that is considered to be final.

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